MPSW05, MPSW06

MPSW06 is a Preferred Device

One Watt Amplifier Transistors

NPN Silicon

ON Semiconductor®

http://onsemi.com

Features

- Pb−Free Packages are Available*

MAXIMUM RATINGS

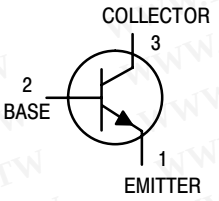
Rating		Symbol	Value	Unit
Collector−Emitter Voltage	MPSW05 MPSW06	V_{CEO}	60 80	Vdc
Collector−Base Voltage	MPSW05 MPSW06	V_{CBO}	60 80	Vdc
Emitter−Base Voltage		V_{EBO}	4.0	Vdc
Collector Current − Continuous		I_C	500	mAdc
Total Device Dissipation @ T_A = 25°C Derate above 25°C		P_D	1.0 8.0	W mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C		P_D	2.5 20	W mW/°C
Operating and Storage Junction Temperature Range		T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

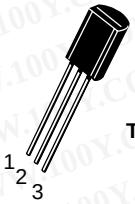
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction−to−Case	$R_{\theta JC}$	50	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

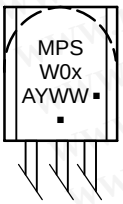
*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



MARKING DIAGRAM



TO−92 (TO−226)
CASE 29−10
STYLE 1



MPSW0x =Device Code
x = 5 or 6
A =Assembly Location
Y =Year
WW =Work Week
▪ =Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MPSW05	TO−92	5,000 Units/Box
MPSW05G	TO−92 (Pb−Free)	5,000 Units/Box
MPSW06	TO−92	5,000 Units/Box
MPSW06G	TO−92 (Pb−Free)	5,000 Units/Box
MPSW06RLRA	TO−92	2,000/Tape & Reel
MPSW06RLRAG	TO−92 (Pb−Free)	2,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Breakdown Voltage (Note 1) (I_C = 1.0 mAdc, I_B = 0)	MPSW05 MPSW06	$V_{(BR)CEO}$	60 80	– –	Vdc
Emitter−Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)		$V_{(BR)EBO}$	4.0	–	Vdc
Collector Cutoff Current (V_{CE} = 40 Vdc, I_B = 0) (V_{CE} = 60 Vdc, I_B = 0)	MPSW05 MPSW06	I_{CES}	– –	0.5 0.5	μAdc
Collector Cutoff Current (V_{CB} = 40 Vdc, I_E = 0) (V_{CB} = 60 Vdc, I_E = 0)	MPSW05 MPSW06	I_{CBO}	– –	0.1 0.1	μAdc
Emitter Cutoff Current (V_{EB} = 3.0 Vdc, I_C = 0)		I_{EBO}	–	0.1	μAdc
ON CHARACTERISTICS (Note 1)					
DC Current Gain (I_C = 50 mAdc, V_{CE} = 1.0 Vdc) (I_C = 250 mAdc, V_{CE} = 1.0 Vdc)		h_{FE}	80 60	– –	–
Collector−Emitter Saturation Voltage (I_C = 250 mAdc, I_B = 10 mAdc)		$V_{CE(sat)}$	–	0.4	Vdc
Base−Emitter Saturation Voltage (I_C = 250 mAdc, V_{CE} = 5.0 Vdc)		$V_{BE(sat)}$	–	1.2	Vdc
SMALL−SIGNAL CHARACTERISTICS					
Current−Gain − Bandwidth Product (I_C = 200 mAdc, V_{CE} = 5.0 Vdc, f = 20 MHz)		f_T	50	–	MHz
Output Capacitance (V_{CB} = 10 V, f = 1.0 MHz)		C_{obo}	–	12	pF

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

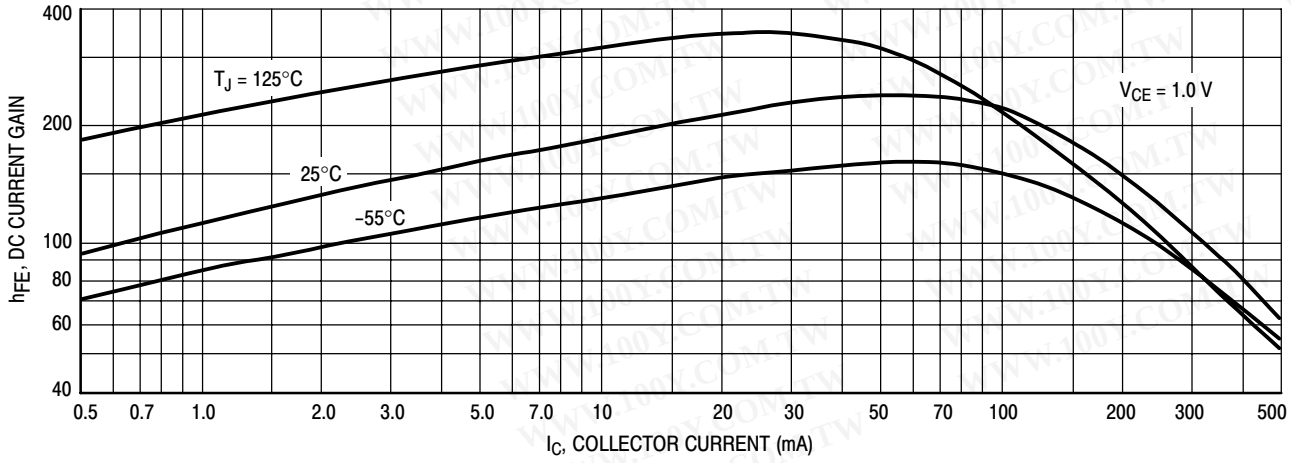


Figure 1. DC Current Gain

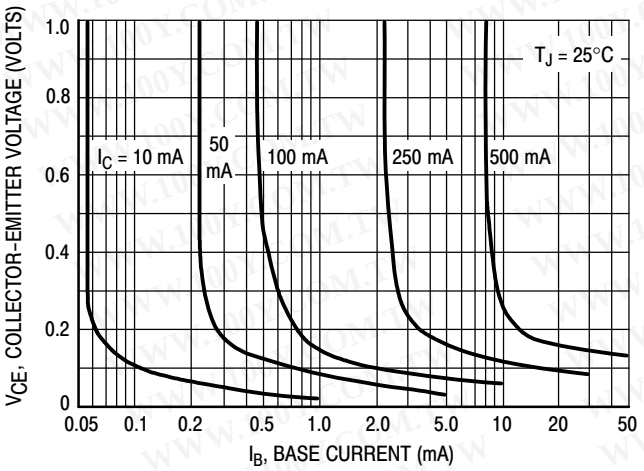


Figure 2. Collector Saturation Region

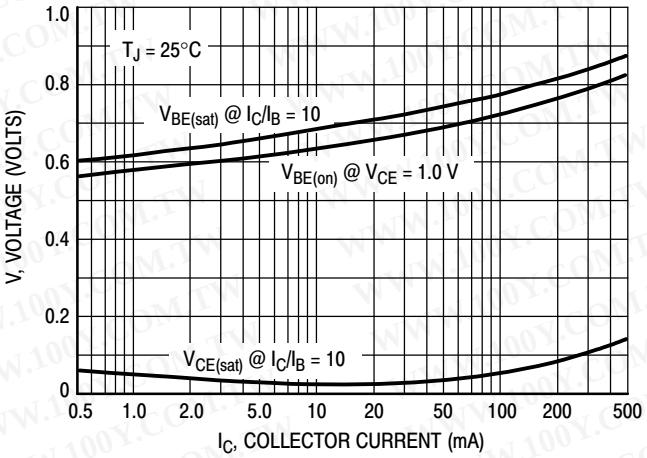


Figure 3. “On” Voltages

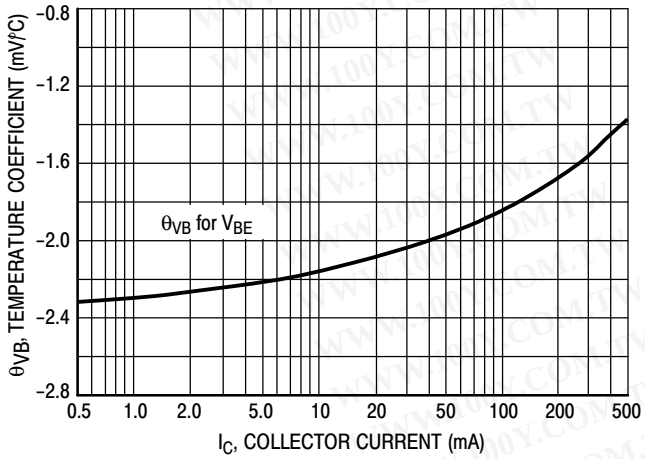


Figure 4. Base−Emitter Temperature Coefficient

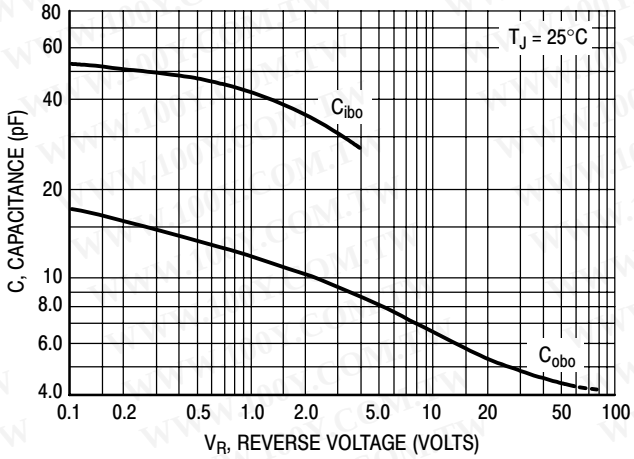


Figure 5. Capacitance

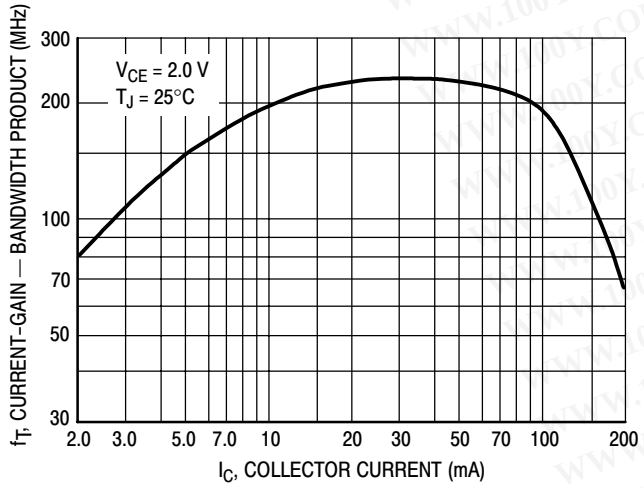


Figure 6. Current−Gain − Bandwidth Product

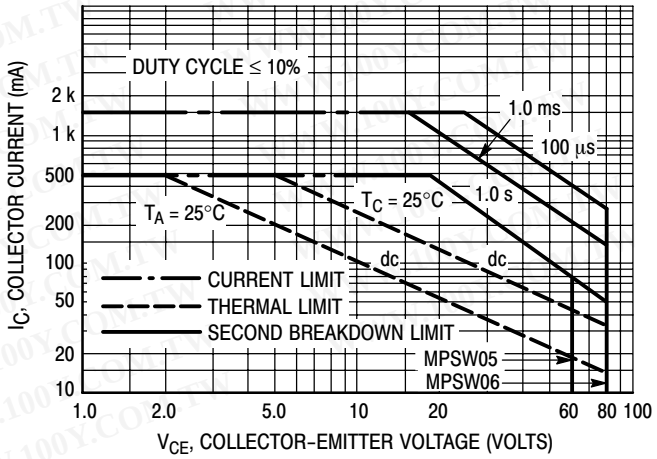
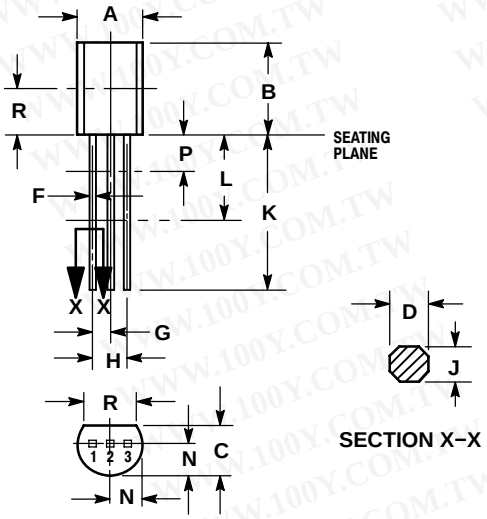


Figure 7. Active Region − Safe Operating Area

PACKAGE DIMENSIONS

TO−92 (TO−226)
CASE 29−10
ISSUE AL



SECTION X−X

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSIONS D AND J APPLY BETWEEN L AND K MIMIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.457	0.533
F	0.016	0.019	0.407	0.482
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

PUBLICATION ORDERING INFORMATION

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